

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 249420US2		SERIAL NO. 10/784,932	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Kazuo NAKAJIMA, et al.			
				FILING DATE February 25, 2004		GROUP 1753	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
ADD	AA	5,437,734	08/01/1995	Takeshi MATSUSHITA, et al.	—	—	
ADD	AB	5,141,564	08/25/1992	Wen S. CHEN, et al.	—	—	
	AC						
	AD						
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	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION		
					YES	NO	
	AO						
	AP						
	AQ						
	AR						
	AS						
	AT						
	AU						
	AV						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
ADD	AW	Kazuo NAKAJIMA, et al., "Growth of Ge-rich, $\text{Si}_x\text{Ge}_{1-x}$ single crystal with uniform composition ($x = 0.02$) on a compositionally graded crystal for use as GaAs solar cells", JOURNAL OF CRYSTAL GROWTH, vol. 205, no. 3, August 1999, pages 270-276					
ADD	AX	Kazuo NAKAJIMA, et al., "Bridgman growth of compositionally graded $\text{In}_x\text{Ga}_{1-x}\text{As}$ ($x = 0.05-0.30$) single crystals for use as seeds for $\text{In}_{0.25}\text{Ga}_{0.75}\text{As}$ crystal growth", JOURNAL OF CRYSTAL GROWTH, vol. 173, no. 1-2, March 1997, pages 42-50					
ADD	AY	J. G. WERTHEN, et al., "Recent Advances In High-Efficiency InGaAs Concentrator Cells", CONFERENCE RECORD OF THE TWENTIETH IEEE PHOTOVOLTAIC SPECIALISTS CONFERENCE, vol.1, September 1988, pages 640-643					
	AZ					<input type="checkbox"/> Additional References sheet(s) attached	
Examiner <i>al D</i>					Date Considered 2/2/06		
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							